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Substitute for form 1448A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	10/035,197
Filing Date	January 4, 2002
First Named Inventor	John Moore
Art Unit	2185
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0488/P488

Sheet 1 of 8

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
C/D	AA	5,761,115	06/02/1998	Kozicki et al.	
	AB	6,084,796	07/04/2000	Kozicki et al.	
	AC	5,914,893	06/22/1999	Kozicki et al.	
	AD	5,896,312	04/20/1999	Kozicki et al.	
	AE	6,388,324	05/14/2002	Kozicki et al.	
	AF	US 2002/0000666	01/03/2002	Kozicki et al.	
	AG	6,500,632	03/19/1996	Kozicki et al.	
	AH	6,418,049	07/09/2002	Kozicki et al.	
	AJ	5,751,012	05/12/1998	Wolstenholme et al.	
	AJ	5,789,277	08/04/1998	Zahorik et al.	
C/D	AK	6,348,365	02/19/2002	Moore et al.	
	AL				
	AM				
	AN				
	AO				

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ³
		Country Code ⁴ -Number ⁴ -Kind Code ⁵ (if known)				
C/D	BA	WO 02/21542	03/14/2002	Kozicki et al.		
	BB	WO 00/48196	08/17/2000	Kozicki et al.		
	BC	WO 97/48032	12/18/1997	Kozicki et al.		
	BD	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature	<i>[Signature]</i>	Date Considered	7/28/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See attached Kind Codes of USPTO Patent Documents at www.uspto.gov or MPEP 601.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
CA	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.	
CB	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
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CD	CD	Affri, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge ₂₅ -xSb _x , Appl. Phys. A 55 (1992) 167-169.	
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CF	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
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CH	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
CI	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
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CR	CR	Bernede, J.C., Switching and silver movements in Ag ₂ Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.	
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CV1	silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.	
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CY1	El Gharradi, R.; Calas, J.; Galibert, G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273.	
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CA2	El-kady, Y.L., The threshold switching in semiconducting glass Ge ₂₁ Se ₁₇ Te ₆₂ , Indian J. Phys. 70A (1998) 507-516.	
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CH3	Iyetomi, H.; Vashishta, P.; Kalia, R.K., Incipient phase separation in Ag/Ge/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.
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CX3	Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GeSe_{1-x} glass, Appl. Phys. Lett. 46 (1985) 543-545.
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